

2SK3269

N-channel enhancement mode MOSFET

■ Features

- Low on-resistance, low Q_g
- High avalanche resistance

■ Applications

- For PDP
- For high-speed switching

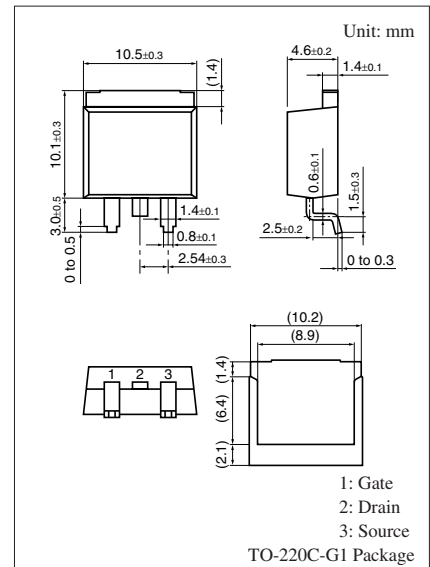
■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain-source surrender voltage	V_{DSS}	100	V
Gate-source surrender voltage	V_{GSS}	± 20	V
Drain current	I_D	± 25	A
Peak drain current	I_{DP}	± 100	A
Avalanche energy capability*	EAS	22.5	mJ
Power dissipation	P_D	40	W
		$T_a = 25^\circ\text{C}$	
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Note) *: $L = 0.2 \text{ mH}$, $I_L = 15 \text{ A}$, 1 pulse

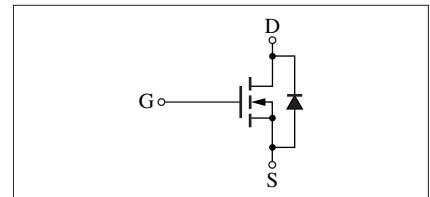
■ Electrical Characteristics $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source surrender voltage	V_{DSS}	$I_D = 1 \text{ mA}$, $V_{GS} = 0$	100			V
Gate threshold voltage	V_{th}	$V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$	2.0		4.0	V
Drain-source cutoff current	I_{DSS}	$V_{DS} = 80 \text{ V}$, $V_{GS} = 0$			10	μA
Gate-source cutoff current	I_{GSS}	$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0$			± 1	μA
Drain-source ON resistance	$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 12 \text{ A}$		70	100	$\text{m}\Omega$
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 10 \text{ V}$, $I_D = 12 \text{ A}$	6	11		S
Short-circuit forward transfer capacitance (Common-source)	C_{iss}	$V_{DS} = 10 \text{ V}$, $V_{GS} = 0$, $f = 1 \text{ MHz}$		960		pF
Short-circuit output capacitance (Common-source)	C_{oss}			285		pF
Reverse transfer capacitance (Common-source)	C_{rss}			85		pF
Turn-on delay time	$t_{d(on)}$		$V_{DD} = 30 \text{ V}$, $I_D = 12 \text{ A}$		15	
Rise time	T_r	$R_L = 2.5 \Omega$, $V_{GS} = 10 \text{ V}$		10		ns
Turn-off delay time	$t_{d(off)}$			65		ns
Fall time	t_f			35		ns



Marking Symbol: K3269

Internal Connection

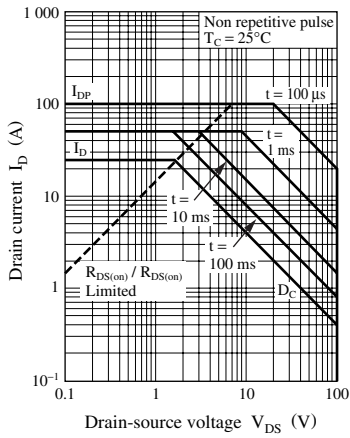


■ Electrical Characteristics (continued) $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

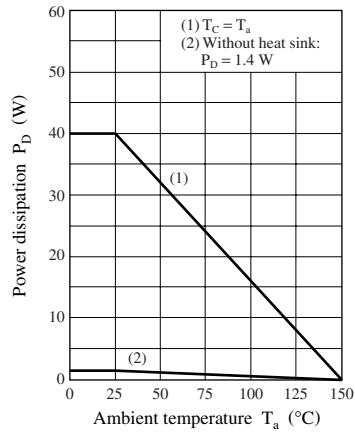
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Diode forward voltage	V_{DSF}	$I_{DR} = 15\text{ A}, V_{GS} = 0$			1.4	V
Thermal resistance (ch-c)	$R_{th(ch-c)}$				3.125	$^\circ\text{C}/\text{W}$
Thermal resistance (ch-a)	$R_{th(ch-a)}$				89.3	$^\circ\text{C}/\text{W}$

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

Safe operation area



$P_D - T_a$



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